

描述 / Descriptions

TO-262 塑封封装 N 沟道 MOS 场效应管。N-CHANNEL MOSFET in a TO-262 Plastic Package..

特征 / Features

低栅电荷,低反馈电容,开关速度快。

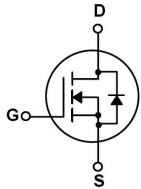
Low gate charge, low crss, fast switching.

用途 / Applications

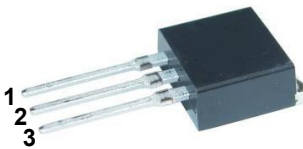
用于高功率 DC/DC 转换和功率开关。

These devices are well suited for high efficiency switching DC/DC converters and switch mode power supplies.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : G

PIN 2 : D

PIN 3 : S

放大及印章代码 / h_{FE} Classifications & Marking

见印章说明。See Marking Instructions.

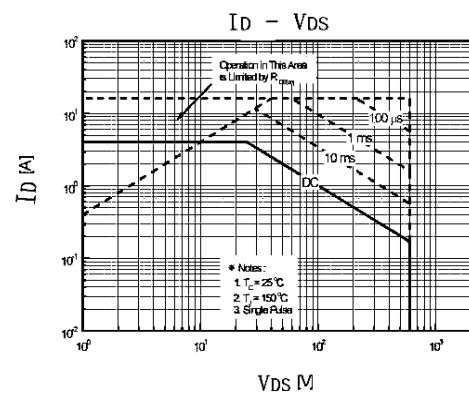
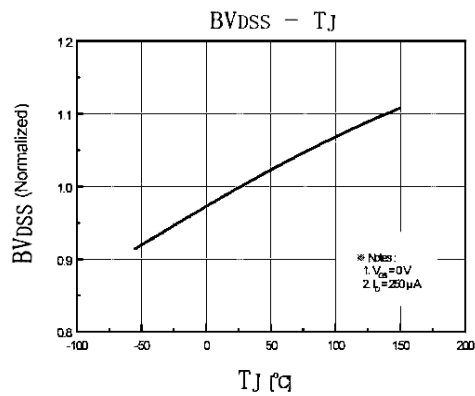
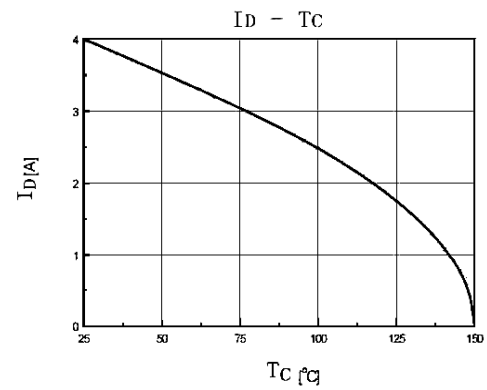
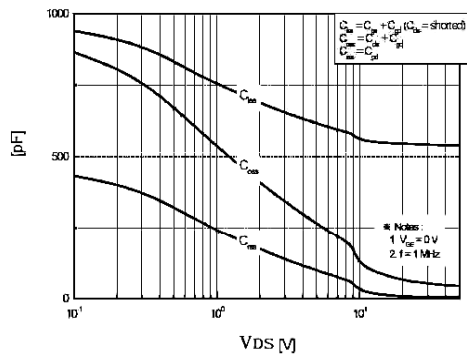
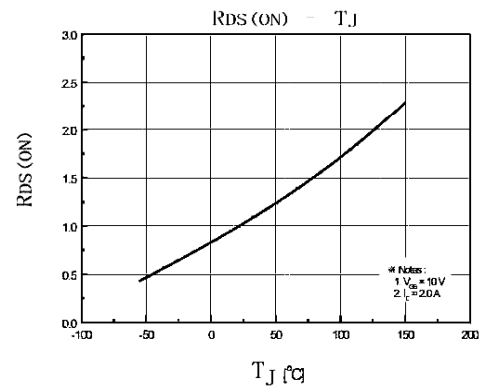
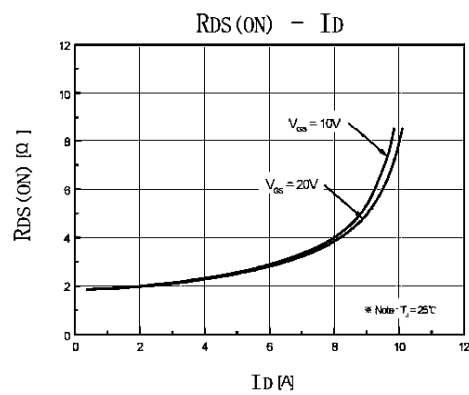
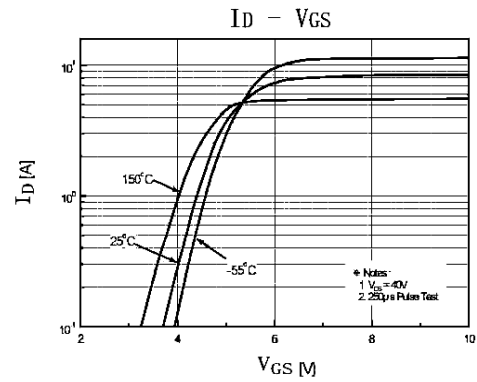
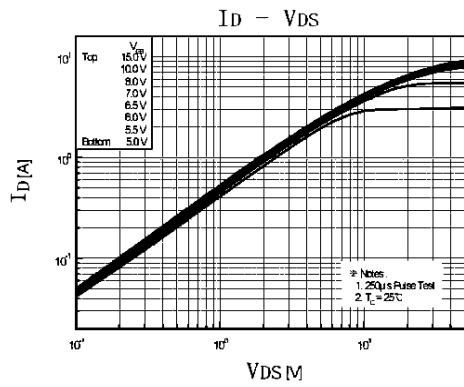
极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Drain-Source Voltage	V_{DSS}	650	V
Drain Current	$I_D(T_C=25^{\circ}C)$	4.0	A
Drain Current	$I_D(T_C=100^{\circ}C)$	2.5	A
Drain Current - Pulsed	I_{DM}	16	A
Gate-Source Voltage	V_{GSS}	± 30	V
Single Pulsed Avalanche Energy	E_{AS}	240	mJ
Repetitive Avalanche Energy	E_{AR}	10	mJ
Avalanche Current	I_{AR}	4.0	A
Power Dissipation	$P_D(T_C=25^{\circ}C)$	50	W
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to 150	$^{\circ}C$

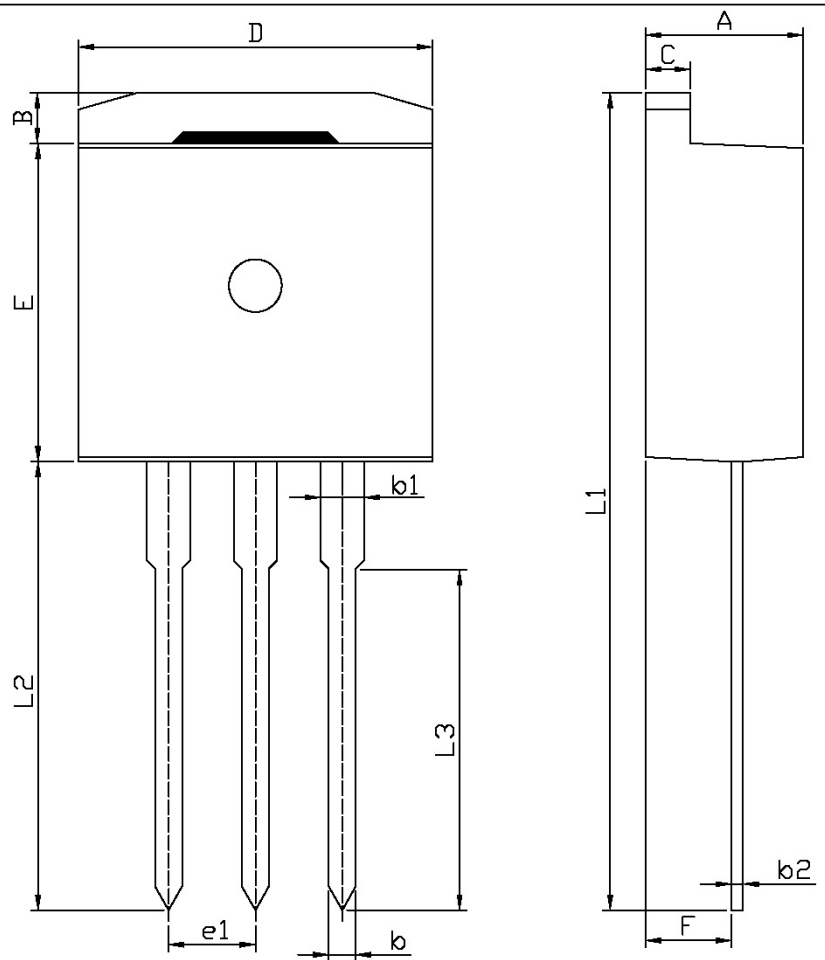
电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V$ $I_D=250\mu A$	650			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=650V$ $V_{GS}=0V$			10	μA
		$V_{DS}=480V$ $T_C=125^{\circ}C$			100	μA
Gate-Body Leakage Current Forward	I_{GSS}	$V_{GS}=\pm 30V$ $V_{DS}=0V$			± 0.1	μA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250\mu A$	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$			3.0	Ω
Forward Transconductance	g_{FS}	$V_{DS}=40V$ $I_D=2.0A$		4.7		S
Drain-Source Diode Forward Voltage	V_{SD}	$V_{GS}=0V$ $I_S=4.0A$			1.4	V
Input Capacitance	C_{iss}	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		545	710	pF
Output Capacitance	C_{oss}			60	80	pF
Reverse Transfer Capacitance	C_{rss}			8	11	pF
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=300V$ $I_D=4.0A$ $R_G=25\Omega$		10	30	ns
Turn-On Rise Time	t_r			35	80	ns
Turn-Off Delay Time	$t_{d(off)}$			45	100	ns
Turn-Off Fall Time	t_f			40	90	ns

电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

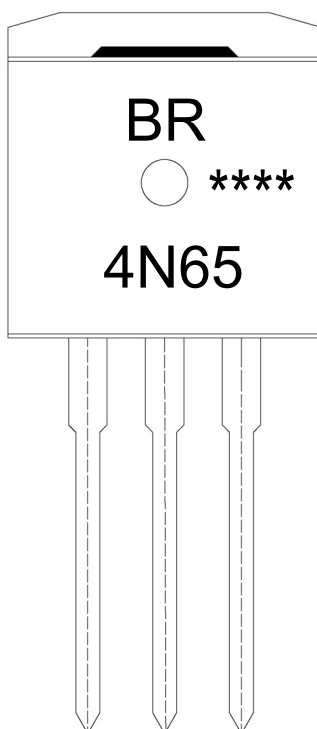


单位: mm

Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.30	4.70	E	9.00	9.40
B	1.00	1.40	e1	2.34	2.74
b	0.70	0.90	F	2.20	2.60
b1	1.27		L1	22.60	23.60
b2	0.40	0.60	L2	12.60	13.60
C	1.20	1.40	L3	9.60	10.60
D	9.80	10.20			

TQ-262

印章说明 / Marking Instructions



说明：

BR： 为公司代码

4N65： 为型号代码

****： 为生产批号代码，随生产批号变化。

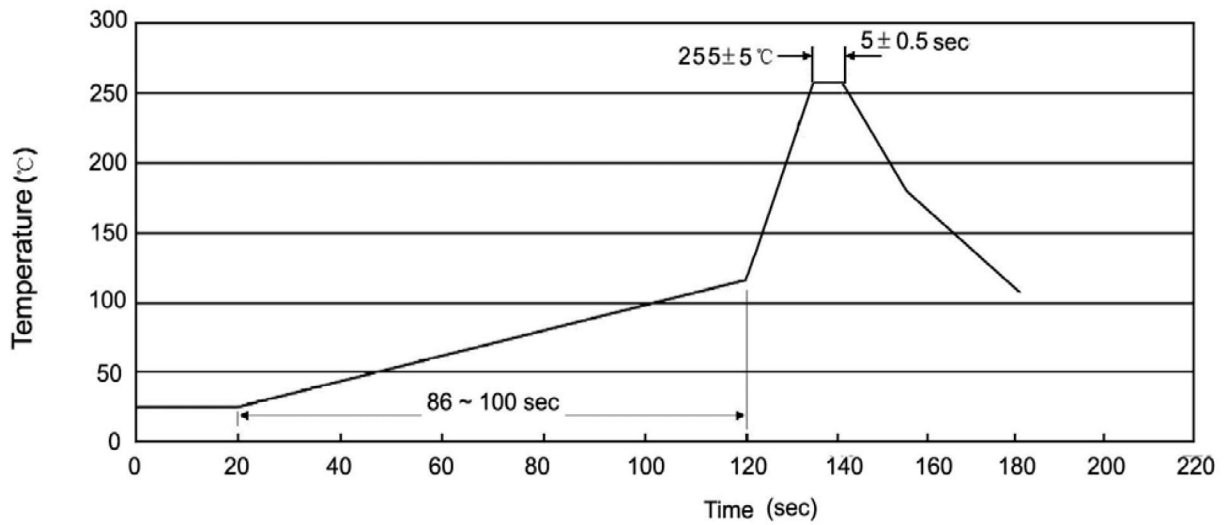
Note:

BR: Company Code

4N65: Product Type.

****: Lot No. Code, code change with Lot No.

波峰焊温度曲线图(无铅) / Temperature Profile for Dip Soldering(Pb-Free)



说明：

- 1、预热温度 25 ~ 150°C，时间 60 ~ 90sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2 ~ 10°C/sec.

Note:

- 1.Preheating:25~150°C, Time:60~90sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：270±5°C

时间：10±1 sec.

Temp.:270±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

套管包装 / TUBE

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
TO-262	50	20	1,000	5	5,000	532×31.4×5.5	555×164×50	575×290×180

使用说明 / Notices